



CHENMKO ENTERPRISE CO.,LTD

Halogens free devices

SURFACE MOUNT

N-Channel Enhancement Mode Field Effect Transistor

VOLTAGE 150 Volts CURRENT 25 Ampere

CHM25N15LPAGP

APPLICATION

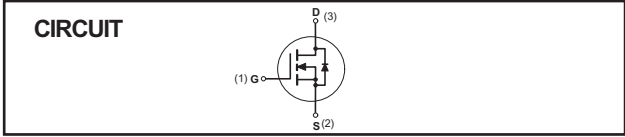
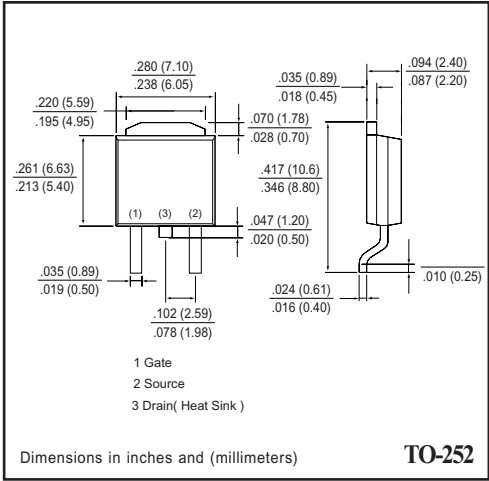
- * Power MOSFET gate drivers.
- * Other switching applications.

FEATURE

- * Small package. (TO-252)
- * Super high dense cell design for extremely low $R_{DS(ON)}$.
- * High power and current handling capability.

CONSTRUCTION

- * N-Channel Enhancement



Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	CHM25N15LPAGP	Units
V_{DSS}	Drain-Source Voltage	150	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Maximum Drain Current - Continuous	25	A
	- Pulsed (Note 3)	100	
P_D	Maximum Power Dissipation at $T_c = 25^\circ\text{C}$	83.3	W
T_J	Operating Temperature Range	-55 to 150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$

- Note : 1. Surface Mounted on FR4 Board , $t \leq 10\text{sec}$
 2. Pulse Test , Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$
 3. Repetitive Rating , Pulse width limited by maximum junction temperature
 4. Guaranteed by design , not subject to production trsting

Thermal characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1)	50	$^\circ\text{C/W}$
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ELECTRICAL CHARACTERISTIC (CHM25N15LPAGP)

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Units
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OFF CHARACTERISTICS

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	125			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 150\text{ V}, V_{GS} = 0\text{ V}$			1	μA
I_{GSSF}	Gate-Body Leakage	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			+100	nA
I_{GSSR}	Gate-Body Leakage	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$			-100	nA

ON CHARACTERISTICS (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1		3	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}, I_D=12\text{A}$ $V_{GS}=5\text{V}, I_D=10\text{A}$		55 60	70 80	$\text{m}\Omega$

Dynamic Characteristics

C_{ISS}	Input Capacitance	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V},$ $f = 1.0\text{ MHz}$		2320		pF
C_{OSS}	Output Capacitance			245		
C_{RSS}	Reverse Transfer Capacitance			30		

SWITCHING CHARACTERISTICS (Note 4)

Q_g	Total Gate Charge	$V_{DS}=120\text{V}, I_D=20\text{A}$ $V_{GS}=10\text{V}$		72	94	nC
Q_{gs}	Gate-Source Charge			5		
Q_{gd}	Gate-Drain Charge			14		
t_{on}	Turn-On Time	$V_{DD}= 75\text{V}$ $I_D = 20\text{A}, V_{GS} = 10\text{ V}$ $R_{GEN}= 1\ \Omega$		16	32	nS
t_r	Rise Time			3	6	
t_{off}	Turn-Off Time			60	120	
t_f	Fall Time			3	6	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS

I_S	Drain-Source Diode Forward Current	(Note 1)			25	A
V_{SD}	Drain-Source Diode Forward Voltage	$I_S = 25\text{A}, V_{GS} = 0\text{ V}$			1.2	V

RATING CHARACTERISTIC CURVES (CHM25N15LPAGP)

Typical Electrical Characteristics

Figure 1. Output Characteristics

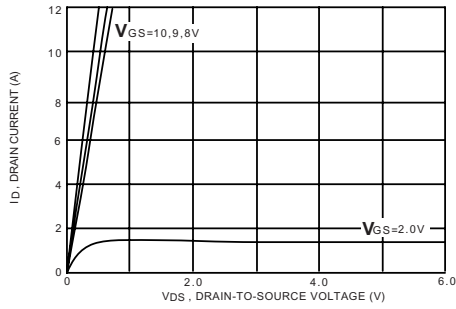


Figure 2. Transfer Characteristics

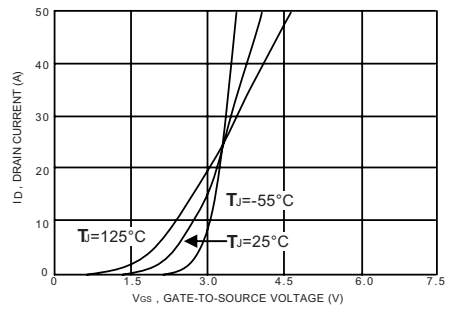


Figure 3. Gate Charge

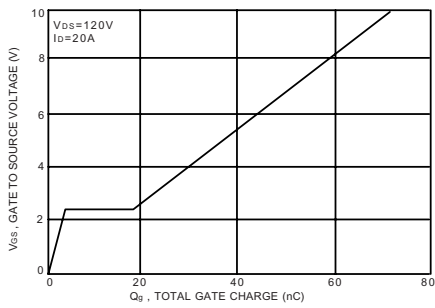


Figure 4. On-Resistance Variation with Temperature

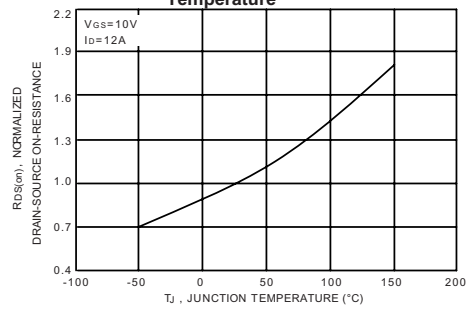


Figure 5. Gate Threshold Variation with Temperature

